

IN THE CLAIMS

Please substitute claims 1-14 with the following:

1. (Currently Amended) A semiconductor device comprising:

a first buried wiring;

a second buried wiring formed as a layer different from said first buried wiring;

a contact hole, ~~which is~~ formed between said first buried wiring and said second buried wiring and is filled with a wiring material electrically connecting said first buried wiring and said second buried wiring therethrough; and

a dummy hole, ~~which has~~ formed to have a hole diameter substantially different from that of said contact hole, ~~is so formed~~ and in the vicinity of said contact hole so that a surface of said first buried wiring is exposed to said dummy hole, ~~and is~~ wherein said dummy hole is adapted to cause a void to form in association with said dummy hole when said dummy hole is at least partially filled with a said wiring material therein.

2. (Currently Amended) The semiconductor device according to claim 1, wherein said second buried wiring is formed ~~as an upper layer of~~ over said first buried wiring, ~~and~~ said dummy hole is formed over said first buried wiring, ~~and has a~~ said diameter of said dummy hole is substantially larger than said contact hole.

3. (Currently Amended) The semiconductor device according to claim 1, wherein said second buried wiring is formed ~~as an upper layer of~~ over said first buried wiring, ~~and~~

dummy hole is formed below said first buried wiring, and ~~has a~~ said diameter of said dummy hole is substantially smaller than said contact hole.

4. (Currently Amended) The semiconductor device according to claim 1, wherein said second buried wiring is formed ~~as a lower layer of~~ under said first buried wiring, and said dummy hole is formed below said first buried wiring and ~~has a~~ said diameter of said dummy hole is substantially smaller than said contact hole.

5. (Currently Amended) The semiconductor device according to claim 1, wherein said second buried wiring is formed ~~as an upper layer of~~ over said first buried wiring, and said dummy hole is formed over said first buried wiring and ~~has a~~ said diameter of said dummy hole is substantially smaller than said contact hole.

6. (Original) The semiconductor device according to claim 1, wherein said wiring material is made of copper.

7. (Currently Amended) The semiconductor device according to claim 3, wherein a said diameter of said dummy hole is so set as to cause a plugging failure to form said void when said dummy hole is at least partially filled with said wiring material.

8. (Currently Amended) The semiconductor device according to claim 4, wherein a said diameter of said dummy hole is so set as to cause a plugging failure to form said void when said dummy hole is at least partially filled with said wiring material.

9. (Currently Amended) The semiconductor device according to claim 5, wherein a said diameter of said dummy hole is so set as to cause a plugging failure to form said void when said dummy hole is at least partially filled with said wiring material.

10. (Currently Amended) A method for manufacturing a semiconductor device including a first buried wiring, a second buried wiring formed ~~as an upper layer of~~ over said first buried wiring, a contact hole, ~~which is~~ formed between said first buried wiring and said second buried wiring and is filled with a wiring material for permitting electric connection between said first buried wiring and said second buried wiring therewith, and a dummy hole, ~~which is so~~ formed over said first buried wiring in the vicinity of said contact hole and ~~has~~ having a hole diameter larger than said contact hole ~~and in which a wiring material is filled~~, the method comprising the steps of:

forming said first buried wiring;

forming an insulating film on said first buried wiring through a diffusion-preventive film and etching the insulating film to simultaneously form said contact hole and said dummy hole in said insulating film so that a surface of said first buried wiring is exposed to a bottom of said dummy hole; and at least partially filling said contact hole and said dummy hole with a wiring

material, respectively such that said dummy hole is adapted to cause a void to form in association with said dummy hole.

11. (Currently Amended) A method for manufacturing a semiconductor device including a first buried wiring, a second buried wiring formed ~~as an upper layer of~~ over said first buried wiring, a contact hole, ~~which is~~ formed between said first buried wiring and said second buried wiring and ~~is~~ filled with a first wiring material for permitting electric connection between said first buried wiring and said second buried wiring therewith, and a dummy hole, ~~which is~~ formed below said first buried wiring in the vicinity of said contact hole and ~~has~~ having a hole diameter smaller than said contact hole ~~and in which a wiring material is filled~~, the method comprising the steps of:

forming a wiring groove for forming said first buried wiring; and
——forming said dummy hole below the wiring groove in such a size as to cause a plugging failure when a second wiring material is at least partially filled in the dummy hole;
burying said dummy hole and said wiring groove with a said second wiring material; ~~and~~
forming the contact hole over said first buried wiring that has been formed by the burying of ~~the~~ said wiring groove with said second wiring material; and
filling said contact hole with a said first wiring material.

12. (Currently Amended) A method for manufacturing a semiconductor device including a first buried wiring, a second buried wiring formed ~~as a lower layer of~~ under said first buried wiring, a contact hole, ~~which is~~ formed between said first buried wiring and said second

buried wiring and is filled with a wiring material for electrically connecting said first buried wiring and said second buried wiring therewith, and a dummy hole, ~~which is~~ formed below said first buried wiring in the vicinity of said contact hole and ~~has~~ having a hole diameter smaller than said contact hole ~~and into which a wiring material is filled~~, the method comprising the steps of:

forming said second buried wiring;

forming said contact hole and said dummy hole over said second buried wiring, said dummy hole in such having a size so as to cause a plugging failure in said dummy hole when a said wiring material is at least partially filled in said dummy hole;

forming a wiring groove for wiring ~~for wiring~~ for forming said first buried wiring in such a condition as to be electrically connected with said contact hole and said dummy hole; and

at least partially filling a said wiring material into the contact hole, the dummy hole, and the wiring groove for wiring ~~for wiring~~, respectively.

13. (Currently Amended) A method for manufacturing a semiconductor device including a first buried wiring, a second buried wiring formed ~~as an upper layer of~~ over said first buried wiring, a contact hole, ~~which is~~ formed between said first buried wiring and said second buried wiring and is filled with a wiring material for electrically connecting said first buried wiring and said second buried wiring therewith, and a dummy hole, ~~which is~~ formed over said first buried wiring in the vicinity of said contact hole and ~~has~~ having a hole diameter smaller than said contact hole ~~and in which a wiring material is filled~~, the method comprising the steps of:

forming said first buried wiring;

forming said contact hole and a dummy ~~pattern~~ hole over said first buried wiring, said dummy hole ~~in such~~ having a size as to cause a plugging failure in said dummy hole when a said wiring material is at least partially filled in said dummy hole;

forming a wiring groove ~~for wiring~~ over said first buried wiring for forming said second buried wiring in such a condition as to be electrically connected with said contact hole and said dummy pattern; and

at least partially filling a said wiring material in said contact hole, said dummy hole, and said wiring groove ~~for wiring~~, respectively.

14. (Currently Amended) A semiconductor device comprising:

a first buried wiring;

a second buried wiring formed as a layer different from said first buried wiring;

a contact hole formed between said first buried wiring and said second buried wiring and filled with a wiring material for electrically connecting said first buried wiring and said second buried wiring therethrough; and

a dummy hole formed in proximity to said contact hole and to have a hole diameter substantially different from that of said contact hole so that a surface of said first buried wiring is exposed to said dummy hole, the dummy hole being at least partially filled with a said wiring material therein such that the dummy hole is operatively configured to inhibit a void from being generated in said contact hole when said first buried wiring is under stress.

15. (New) The semiconductor device according to claim 1, wherein said dummy hole is formed within a distance of said contact hole corresponding to twenty times said diameter of said contact hole.

16. (New) The semiconductor device according to claim 1, wherein said dummy hole is formed within 1 μm of said contact hole.

17. (New) The semiconductor device according to claim 2, wherein said diameter of said dummy hole is equal to or greater than 0.2 μm .

18. (New) The semiconductor device according to claim 3, wherein said diameter of said dummy hole is equal to or less than 0.12 μm .

19. (New) The semiconductor device according to claim 4, wherein said diameter of said dummy hole is equal to or less than 0.12 μm .